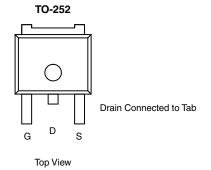


www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0036				
I _D (A)	100				
Configuration	Single				



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualifieddd
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



	D
G —	
N-Channel MOSFET	O S

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD100N04-3m6-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current	T _C = 25 °C ^a	1	100		
	T _C = 125 °C	I _D	76		
Continuous Source Current (Diode Conduction	I _S	100	Α		
Pulsed Drain Current ^b		I _{DM}	400		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	62		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	192	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	- P _D	136		
	T _C = 125 °C		45	W	
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°CAM	
Junction-to-Case (Drain)		R _{thJC}	1.1	°C/W	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						ı	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		-	3.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	1
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0030	0.0036	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0063	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0076	
Forward Transconductanceb	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 15 A		120	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz	ı	5360	6700	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		-	500	627	
Reverse Transfer Capacitance	C _{rss}			ı	250	310	
Total Gate Charge ^c	Qg			ı	70	105	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$	-	16	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	13	-	
Gate Resistance	R_{g}		f = 1 MHz		1.86	2.8	Ω
Turn-On Delay Time ^c	t _{d(on)}				11	16	
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 0.4 Ω $I_D \cong$ 50 A, V_{GEN} = 10 V, R_g = 1 Ω		-	5	8	ns
Turn-Off Delay Time ^c	t _{d(off)}			ı	34	51	
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			1	-	400	Α
Forward Voltage	V_{SD}	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$		-	0.9	1.5	V

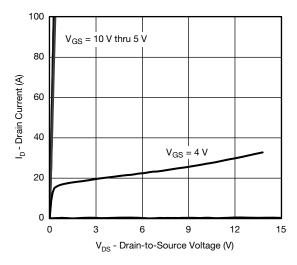
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

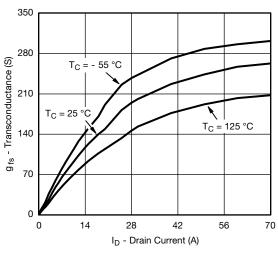
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



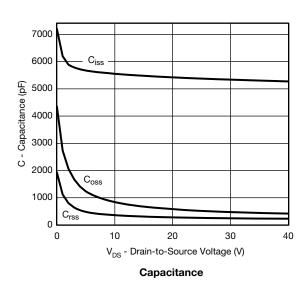
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

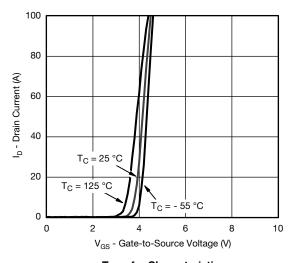


Output Characteristics

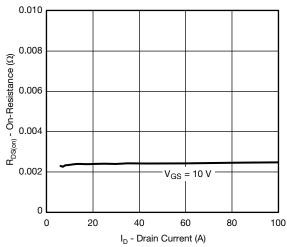


Transconductance

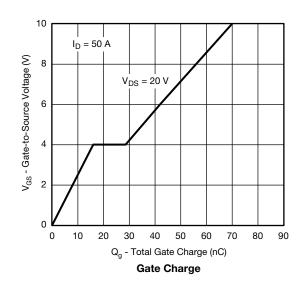




Transfer Characteristics



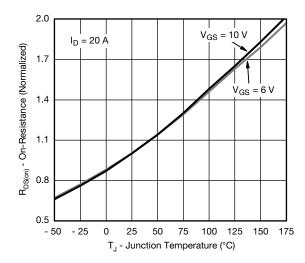
On-Resistance vs. Drain Current



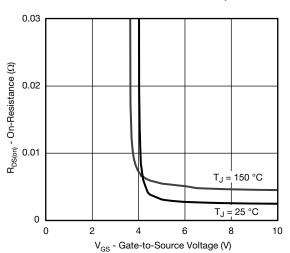
Document Number: 63836



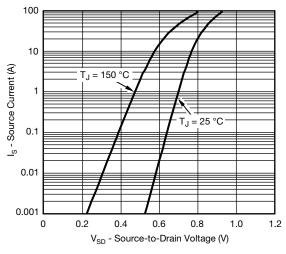
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



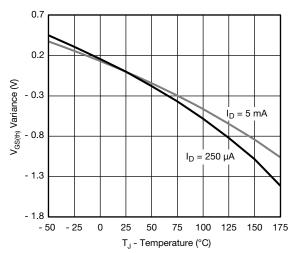
On-Resistance vs. Junction Temperature



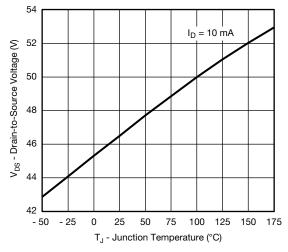
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



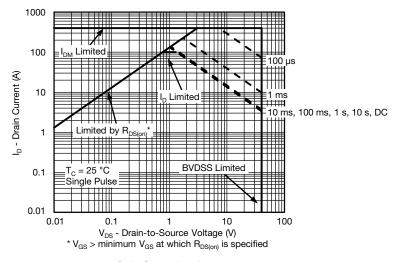
Threshold Voltage



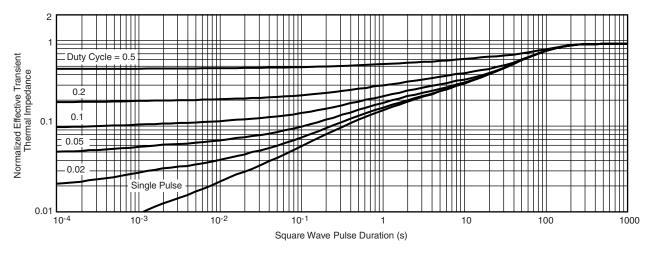
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



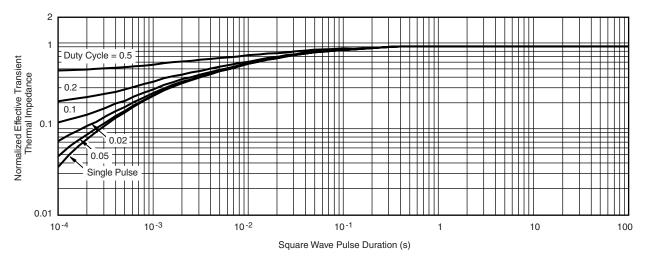
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

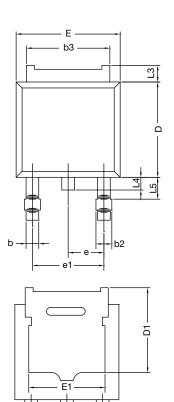
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

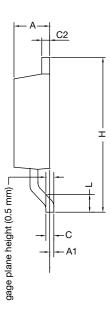
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TO-252AA Case Outline





	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

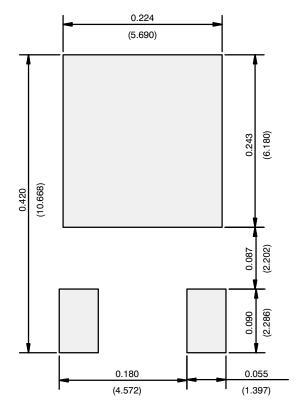
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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